

## **KSC1675**

### FM/AM RF AMP, MIX, CONV,OSC,IF

- Collector-Base Voltage: V<sub>CEO</sub>=30V
  High Current Gain Bandwidth Product: f<sub>T</sub>=300MHz (TYP.)
- Low Collector Capacitance : C<sub>OB</sub>=2.0pF (TYP.)
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



## **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	50	mA
P <sub>C</sub>	Collector Power Dissipation	250	mW
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C}=10\mu A, I_{E}=0$	50			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C=5mA$ , $I_B=0$	30			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E}=10\mu A, I_{C}=0$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =50V, $I_E$ =0			0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =5V, $I_{C}$ =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE}$ =6V, $I_{C}$ =1mA	40		240	
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ =6V, $I_{C}$ =1mA		0.67	0.75	V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.08	0.3	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE}$ =6V, $I_{C}$ =1mA	150	300		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =6V, I <sub>E</sub> =0, f=1MHz		2.0	2.5	pF

## **h**<sub>FE</sub> Classification

Classification	R	0	Y
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240

# **Typical Characteristics**

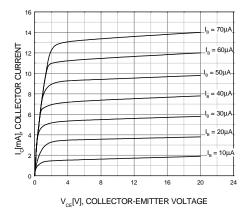


Figure 1. Static Charactersitic

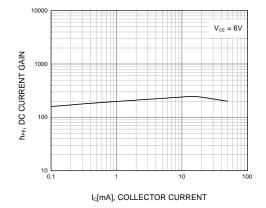


Figure 2. DC current Gain

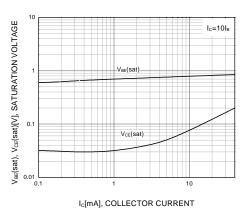


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

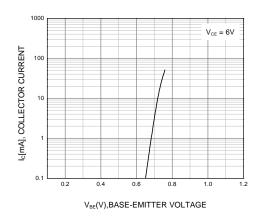


Figure 4. Base-Emitter On Voltage

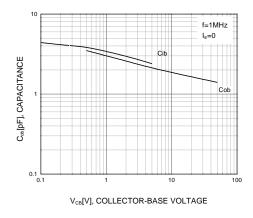


Figure 5. Input Output Capacitance

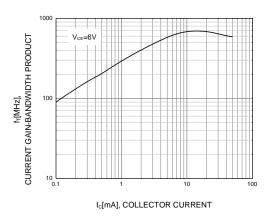
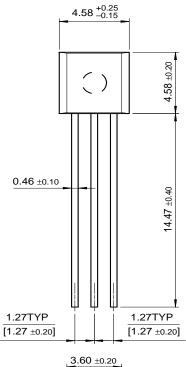


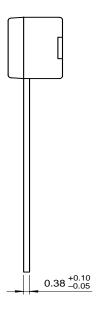
Figure 6. Current Gain Bandwidth Product

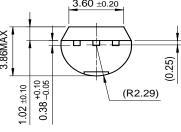
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# **Package Dimensions**

TO-92







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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
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EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
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